

Theoretical evidence for efficient p -type doping of GaN using beryllium

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Ab initio calculations predict that Be is a shallow acceptor in GaN. Its thermal ionization energy is 0.06 eV in wurtzite GaN; the level is valence resonant in the zincblende phase. Be incorporation is severely limited by the formation of Be_3N_2 . We show however that co-incorporation with reactive species can enhance the solubility. H-assisted incorporation should lead to high doping levels in MOCVD growth after post-growth annealing at about 850 K. Be-O co-incorporation produces high Be and O concentrations at MBE growth temperatures.

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Gallium nitride is a base material for green-to-UV optoelectronics, and piezoelectric and high-power devices. For these applications, controllable doping is an obvious necessity. Si_{Ga} is a suitable shallow donor, but the quest for the optimal acceptor still continues. The current-best p -dopant [1] is Mg_{Ga} , with which hole concentrations in the 10^{17} cm^{-3} range have been achieved at room temperature (despite its ionization energy of ~ 0.2 eV), and whose activation mechanism is still under scrutiny [2].

We show here that substantial improvements can be achieved by doping GaN with Be: ab initio calculations of formation energies, impurity levels, and atomic geometries of Be in GaN show that Be is the shallowest acceptors reported so far in GaN. Calculated solubilities indicate barely acceptable doping levels in N-rich growth conditions at high growth temperatures, while complete compensation occurs in Ga-rich conditions due to N vacancies. We show however that the co-incorporation of Be with H or O strongly enhances its solubility (otherwise limited by the formation of Be nitride) and may lead to p -type doping.

Method – By means of density-functional-theory (DFT) [3] ultrasoft-pseudopotential plane-wave calculations of total energies and forces in doped GaN (details are reported elsewhere [1,4,5]), we predict from first principles the formation energies and thermal ionization energies, and ensuing dopant and carrier concentrations of Be in GaN. The carriers concentration at temperature T due to a single acceptor with thermal ionization energy $\epsilon[0/-]$ is

$$n = D \exp(-\epsilon[0/-]/k_{\text{B}}T) \equiv D\mathcal{E}. \quad (1)$$

The impurity concentration D in thermal equilibrium is

$$D = N_s \exp(-E_{\text{form}}/k_{\text{B}}T_g) \quad (2)$$

for a growth temperature of T_g , with $N_s = 4.33 \times 10^{22} \text{ cm}^{-3}$ available sites, and a formation energy E_{form} . Omission of the entropic factor $\exp(S_f/k_{\text{B}})$ (formation entropies are currently impossible to calculate reliably) does not alter our conclusions. The formation energy for Be_{Ga} in charge state Q is

$$E_{\text{form}}(Q) = E^{\text{tot}}(Q) - \sum_X n^X \mu^X + Q(\mu_e + E_v^Q), \quad (3)$$

where μ_e is the electron chemical potential, $E^{\text{tot}}(Q)$ is the total energy of the defected supercell in charge state Q , E_v^Q its top valence band energy, n^X and μ^X the number of atoms of the involved species ($X=\text{Ga}, \text{N}, \text{Be}$) and their chemical potentials. The latter potentials must satisfy the equilibrium conditions with GaN and Be- X compounds. To obtain maximum solubility, we will always be choosing the highest μ^{Be} compatible with the relevant solubility limit. Then, a single chemical potential (e.g. μ^{N}) remains to be determined by the imposed (N-rich \leftrightarrow Ga-rich) growth conditions. Since $T=0$ in our calculations, μ_e is synonymous with the Fermi energy.

The thermal ionization level $\epsilon[0/-]$ of a single acceptor is by definition the formation-energy difference of the two charge states $Q=0$ and $Q=-1$ at $\mu_e=0$. Thermal ionization corresponds to hole release from (i.e., electron promotion into) the acceptor extrinsic state with concurrent geometric relaxation. Optical transition energies can be obtained as e.g. $E_{\text{gap}} - \epsilon[0/-] - E_{\text{FC}}$ for conduction band-to-acceptor recombination. E_{FC} is the Franck-Condon shift for the $Q=-1$ state in the equilibrium geometry of the $Q=0$ state. For Be, $E_{\text{FC}} = 0.04$ eV [5].

The above quantities are DFT total energy differences and as such exact in principle, were it not for the local density approximation [3] and other technicalities. Among the latter, the one introducing the largest uncertainty is the alignment of the energy zeroes for the different charge states. The resulting error bar is typically ± 0.1 eV in the ionization energies, but in fact lower (~ 0.05 eV) for Be_{Ga} (see Refs. [1,4] for details).

Results – The thermal level of Be_{Ga} is 0.06 eV in wurtzite GaN. This value agrees well with our previous estimate [5] based on a different (and less accurate) technique. In the zincblende phase, the level is found to be resonant with the valence band. The difference between

zincblende and wurtzite is due to symmetry-related electronic structure features, namely the impurity state being mostly localized on *all* the four impurity-neighboring N atoms in zincblende, while only on the *a*-plane neighbors in wurtzite (see Ref. [4] for more). Despite this minor deviation, the overall energetics is essentially the same in the two phases (the numbers below are for wurtzite).

Be_{Ga} is a shallow dopant in GaN, with an activation efficiency $\mathcal{E} \sim 0.1$ (see Eq.1) at room temperature. To evaluate its chemical concentration, we calculated its formation energy as a function of growth conditions and of the Fermi energy (accounting for the dependence of the latter on charge neutrality conditions [6] involving background doping and competing defects). For neutral Be, E_{form} is 2.29 eV (2.83 eV) in N-rich (Ga-rich) conditions; for $\mu_e > \epsilon[0/-]$, the negative state is favored ($E_{\text{form}}=2.35$ eV $- \mu_e$). These high formation energies stem from the strict solubility limit imposed by the formation of Be₃N₂ (whose total energy is also calculated ab initio). Therefore, the Be concentration achievable in GaN is typically quite low. Also, competing defect configurations exist: we considered the nitrogen vacancy V_N, two kinds of interstitial Be (in the wurtzite channels and in the “trigonal” cage), and heteroantisite Be_N (the latter being ruled out by a formation energy of ~ 8 eV).

The most favorable growth condition for Be_{Ga} incorporation is *N-rich*. V_N⁺ is an ionized single donor with a formation energy of $2.32 + \mu_e$ (possibly behaving as multiple donor in the extreme *p* limit [2]). The Be interstitials are double donors over most of the relevant Fermi level range (since $\epsilon[2 + /+] \sim 2.3$ eV), with formation energies of 2.39 eV $+ 2 \mu_e$ (cage) and 2.43 eV $+ 2 \mu_e$ (channel). Therefore, none of these defects is ever competitive with Be_{Ga}⁰ ($E_{\text{form}}=2.29$ eV) or Be_{Ga}⁻ ($E_{\text{form}}=2.35$ eV $- \mu_e$). In particular, compensation by V_N⁺ is suppressed. However, at typical MOCVD growth temperatures of 1500 K, the maximum concentrations reached is only $D \simeq 10^{17} - 10^{18}$ /cm³ assuming formation entropies between zero and 5 k_B (the entropic factor enhances the solubility). In wurtzite GaN at room temperature, thanks to Be’s shallowness, this implies a doping level of $10^{16}-10^{17}$ cm⁻³. For comparison, the calculated concentration [4] of Mg_{Ga} in the same conditions is about 10^{19} /cm³ ($E_{\text{form}}=1.40$ eV), but the carrier concentration is low because of $\mathcal{E} \sim 10^{-4}$ (Eq.1) at room temperature, as implied by the calculated ionization energy of 0.23 eV.

In *Ga-rich* conditions the situation is more critical. The formation energy of V_N⁺ is 0.67 eV $+ \mu_e$, whereas that of Be_{Ga}⁻ is $2.89 - \mu_e$. This results in complete compensation, with the Fermi level pinned at about 1.1 eV above the valence band top. The interstitials, again double donors with formation energies of 1.29 eV $+ 2 \mu_e$ (cage) and 1.33 eV $+ 2 \mu_e$ (channel), are competitive with Be_{Ga} only in *p*-type conditions (Fermi levels below ~ 0.4 eV). Their action is anyway preempted by V_N⁺, which pins the Fermi level much higher in the gap.

Co-incorporation – As shown earlier, Be *alone* could never be incorporated massively in GaN. An abundant supply of Be in the growth process would eventually cause Be₃N₂ to form, with detrimental effects for GaN crystal quality [7]. A possible way to enhance the solubility of Be in GaN is “incorporation catalysis” by reactive species.

We consider first the H-assisted incorporation suggested recently [2] for Mg. The formation energy of a (neutral) Be-H complex in its equilibrium configuration in GaN is 0.32 (0.87) eV/complex in N-rich (Ga-rich) conditions (solubility limits: Be₃N₂ and H₂ molecules): the concurrent incorporation of Be and H in GaN is therefore efficient. Accounting for competing species and charge neutrality, we find that as much as 10^{19} to 10^{21} Be’s and H’s per cm³ get incorporated in the Ga-rich and N-rich limits respectively, at a growth temperature of 1500 K.

However, the acceptor is compensated by H, which must be eliminated from the sample to activate *p*-type conduction. After H is detached from the complex, Be is still compensated, since H is in its positive charge state [5,8]. H should thus be removed from the *p*-doped region by annealing in e.g. a N₂ atmosphere. Being quite stable, the Be-H complex is easy to incorporate but difficult to break up: the minimum binding energy difference between Be-H and isolated Be_{Ga}⁻ plus isolated H⁺ in its equilibrium configuration (N backbonding site) is 1.8 eV [5,9]. We estimate the barrier for detachment to be at least of order 2.1 eV. Within a simple desorption-like description, the annealing temperature T_{ann} needed to break up H-Be complexes may be estimated from the rate

$$R \simeq \nu \exp(-E_{\text{barr}}/k_B T_{\text{ann}}).$$

The relevant attempt frequency ν is that of the H-Be bond center wagging mode, since the complex ground state is H at a Be-N bond center [5]. We have previously calculated [5] the stretching frequency for the H-Mg complex to be about 3000 cm⁻¹ in the equilibrium N-backbonding site; as this Mg-H frequency essentially originates from N-H pairing [5,8], it is expected to be similar for H-Be. As wagging frequencies of H at bond centers are usually about 10 times lower than stretching frequencies [10], we pick $\nu=100$ THz ~ 300 cm⁻¹. With these parameters, massive break-up of H-Be sets in at about 850 K, which seems a practicable post-processing temperature.

Be-H co-incorporation seems possible. The analogous idea of reactive co-doping [11] also appears to be useful. In recent experiments [11], Be and O concentrations in the 5×10^{20} cm⁻³ range have been reported in zincblende GaN grown by MBE at 950 K in moderately N-rich and oxygen-contaminated conditions. Importantly, experiment [11] indicates that Be prevails over O by about 20 % ($D[\text{Be}] = 5 \times 10^{20}$ cm⁻³, $D[\text{O}] = 4 \times 10^{20}$ cm⁻³), leading to *p*-type doping.

We find that the co-incorporation of Be and O favors the precipitation of BeO over the formation of the individual solubility-limiting compounds Be_3N_2 and Ga_2O_3 , because the reaction



is strongly exothermic (6.4 eV). Therefore, Be and O can be incorporated *concurrently* in large amounts into GaN. However, the incorporation of Be *in excess of* O (as it appears to occur in the co-doping experiments [11]) is still affected by the Be_3N_2 solubility limit, so that the net Be concentration cannot be larger than that obtained in the absence of O. In consideration of the above-cited experimental evidence by Brandt *et al.* [11], our results, obtained assuming the validity of equilibrium thermodynamics, imply that non-equilibrium effects are operative in the actual co-doping process. Such as-yet unknown effects may be related to growth kinetics, as is quite plausible considering the highly non-equilibrium nature of the MBE growth process.

One may speculate that the presence of high chemical concentrations of Be (albeit O-compensated) will make it more likely for small non-equilibrium concentration fluctuations to occur in an interesting range (say $\sim 10^{19} \text{ cm}^{-3}$, i.e. $\sim 5\%$ of the total concentration), whatever the exact cause of such fluctuations. This hypothesis is especially intriguing, since the same mechanism may apply to III-V nitrides in general: we found in fact that exothermic reactions analogous to Eq. (4) hold for several Group-II dopants (Be, Zn, Mg, Ca) in AlN and InN as well as in GaN, so that O-acceptor co-incorporation will occur efficiently in most cases. A treatment of this issue is beyond the scope of this work, and is deferred to a future work.

We note that calculations show also that a neutral BeO pair substituting for a GaN pair is bound by 1.0 eV/pair with respect to over isolated Be_{Ga}^- and O_{N}^+ : this path for O-Be donor-acceptor compensation may thus be preferred over hole-electron recombination. BeO pairs carry at most a dipole, which scatters carriers less efficiently than a charged center. An enhanced carrier mobility should ensue, in qualitative agreement with unusually high mobilities being observed in experiment [11].

In summary, ab initio calculations predict that Be is a shallow acceptor in GaN. Be solubility in GaN is low due to Be_3N_2 formation, so that hole concentrations at room temperature of only $\sim 10^{17} \text{ cm}^{-3}$ are obtained from N-rich, high-temperature growth. In Ga-rich conditions, vacancy-acceptor compensation produces semi-insulating material. The presence of H enhances Be solubility in GaN, although acceptor activation requires annealing at about 850 K. Our finding of massive co-incorporation of O and Be in GaN grown in an O-contaminated atmosphere confirms in part the results of recent experiments [11]. In conclusion, further consideration of Be in actual

growth experiments may open the way to a more effective *p*-doping of GaN.

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